

- AVAILABLE IN JAN, JANTX, AND JANTXV
PER MIL-PRF-19500/118
- GENERAL PURPOSE SILICON DIODES
- METALLURGICALLY BONDED

1N5194
1N5195
1N5196

MAXIMUM RATINGS

Operating Temperature: -65°C to +175°C
Storage Temperature: -65°C to +175°C
Operating Current: 200 mA
Derating: 1.2 mA/°C From 25°C to 150°C
1.0 mA/°C From 150°C to 175°C
Forward Current: 650 mA

ELECTRICAL CHARACTERISTICS @ 25°C, unless otherwise specified

TYPE	V _{RM}	V _{RWM}	I _O	I _O	I _{FSM}
	V (pk)	V (pk)	mA	mA	A
1N5194	80	70	200	50	2
1N5195	180	180	200	50	2
1N5196	250	225	200	50	2

TYPE	V _F @100mA	I _{R1} at V _{RWM} T _A = 25°C	I _{R2} at V _{RM} T _A = 25°C	I _{R3} at V _{RWM} T _A = 150°C
	V dc	nA dc	µA	µA dc
1N5194	0.8 - 1.0	25	100	5
1N5195	0.8 - 1.0	25	100	5
1N5196	0.8 - 1.0	25	100	5

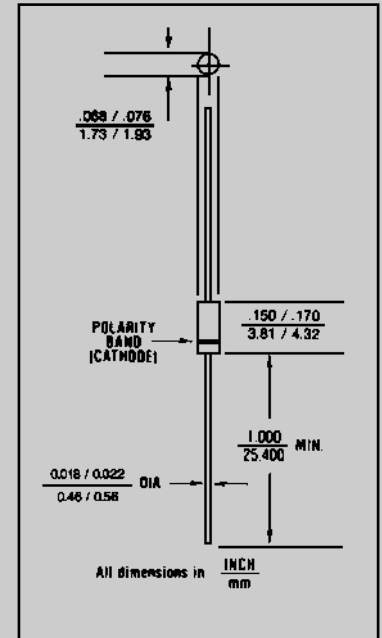


FIGURE 1

DESIGN DATA

CASE: Hermetically sealed glass case. DO - 35 outline.

LEAD MATERIAL: Copper clad steel.

LEAD FINISH: Tin / Lead

THERMAL RESISTANCE: (R_{ΘJC}): 250 °C/W maximum

THERMAL IMPEDANCE: (Z_{ΘJX}): 70 °C/W maximum

POLARITY: Cathode end is banded.

MOUNTING POSITION: ANY.



IN5194 thru IN5196

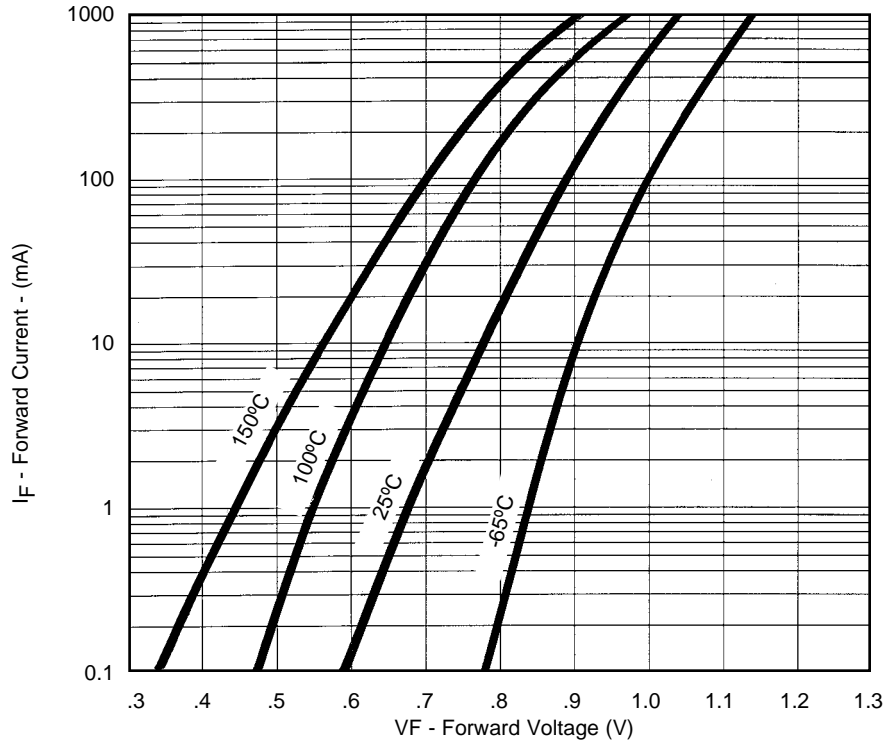
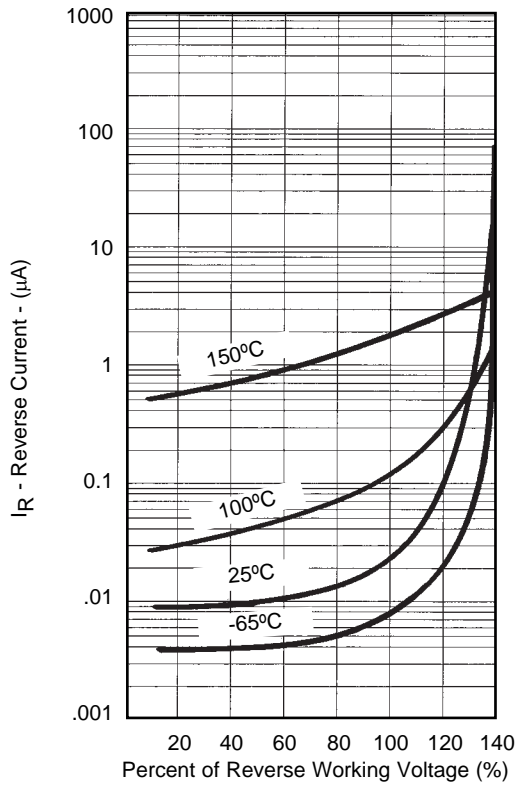


FIGURE 2
Typical Forward Current
vs Forward Voltage



NOTE : All temperatures shown on graphs are junction temperatures

FIGURE 3
Typical Reverse Current
vs Reverse Voltage